EL2223D Die

Dual, 500 MHz, High Speed Operational Amplifier

Absolute Maximum Ratings (TA = 25°C)

LINSU	idle maximum itamigs	(1A - 25 C
v_s	Voltage between V+ and V-	
ΔV_{IN}	Differential Input Voltage	6V
IOP	Output Current, Peak	50 mA
I _{OC}	Output Current, Continuous	25 mA
Tr	Maximum Junction Temperature	175°C

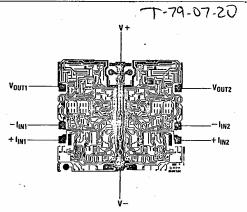
Important Note:

For AC electrical characteristics, refer to the typical electrical table and performance curves in the package data sheet. These characteristics are guaranteed but not tested in die form. Unless otherwise noted, all tests are pulsed tests, therefore $T_J = T_C = T_A$.

Test Level

Test Procedure

100% production tested in wafer form. See remarks under Electrical Testing in the General Die section.



DIE SIZE: 85 x 71 MILS



DC Electrical Characteristics $v_S = \pm 15V$, $R_L = 2 k\Omega$, $T_A = 25^{\circ}C$

Parameter	Description	Min	Тур	Max	Test Level	Units
vos	Offset Voltage		0.5	5	24/11/	mV
ľ _B	Bias Current		1.5	4	i i i	μΑ
Ios	Offset Current		0.2	2		μA
V _{CM}	Common Mode Range	±10	±12			v
A _{VOL}	Large Signal Voltage Gain (Note 1)	20k	40k		\$ X I	V/V
CMRR	Common-Mode Rejection Ratio (Note 2)	70	90		1	ďΒ
v _o	Output Voltage Swing	±11	±12.5		11/2	v
I _O	Output Current		±50	±70	125 YI (145)	mA
IS	Supply Current		9.5	13	i	mA
PSRR	Power Supply Rejection Ratio (Note 3)	70	90		I	dB

Note 1: $V_O = \pm 10V$.

Note 2: Two tests are performed. $V_{CM} = 0V$ to +10V and $V_{CM} = 0V$ to -10V.

Note 3: Two tests are performed. V + = +15V, and V -is changed from -5V to -15V. V - = -15V, and V +is changed from +5V to +15V.